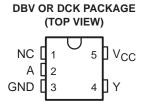
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- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Input and Open-Drain Output Accepts Voltages up to 5.5 V
- Supports 5-V V_{CC} Operation
- Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages



NC - No internal connection

description

This single inverter buffer/driver is designed for 1.65-V to 5.5-V V_{CC} operation.

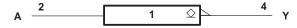
The output of the SN74LVC1G06 device is open drain and can be connected to other open-drain outputs to implement active-low wired-OR or active-high wired-AND functions. The maximum sink current is 32 mA.

The SN74LVC1G06 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

INPUT A	OUTPUT Y
Н	L
L	Н

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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SN74LVC1G06 SINGLE INVERTER BUFFER/DRIVER WITH OPEN-DRAIN OUTPUT

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Output voltage range, VO (see Notes 1 and 2)	\dots -0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DBV package .	206°C/W
DCK package .	252°C/W
Storage temperature range, T _{sto}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

			MIN	MAX	UNIT	
Vcc	Supply voltage	Operating	1.65	5.5	V	
		Data retention only	1.5		V	
	High have Constructions	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$			
] ,,		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
VIH	High-level input voltage	$V_{CC} = 3 V \text{ to } 3.6 V$	2		V	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}			
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		
VIL	Low-level input voltage	V _{CC} = 2.3 V to 2.7 V		0.7	.,	
		V _{CC} = 3 V to 3.6 V		0.8	V	
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}		
VI	Input voltage	0	5.5	V		
Vo	Output voltage		0	VCC	V	
		V _{CC} = 1.65 V		4		
	Low-level output current	V _{CC} = 2.3 V		8		
lOL		V 2V		16	mA	
		VCC = 3 V		24		
		V _{CC} = 4.5 V		32		
	Input transition rise or fall rate	$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20		
Δt/Δν		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
		V _{CC} = 5 V ± 0.5 V	V _{CC} = 5 V ± 0.5 V			
T _A	Operating free-air temperature		-40	85	°C	



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	VCC	MIN TYPT MAX	UNIT
	I _{OL} = 100 μA	1.65 V to 5.5 V	0.1	
	I _{OL} = 4 mA	1.65 V	0.45	
,,	I _{OL} = 8 mA	2.3 V	0.3	V
VOL	I _{OL} = 16 mA	2.1/	0.4	
	I _{OL} = 24 mA	3 V	0.55	
	I _{OL} = 32 mA	4.5 V	0.55	
lį	V _I = 5.5 V or GND	0 to 5.5 V	±5	μΑ
ICC	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V	10	μΑ
ΔlCC	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V	500	μΑ
C _i	$V_I = V_{CC}$ or GND	3.3 V	4	pF
Co	$V_O = V_{CC}$ or GND	3.3 V	5	pF

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

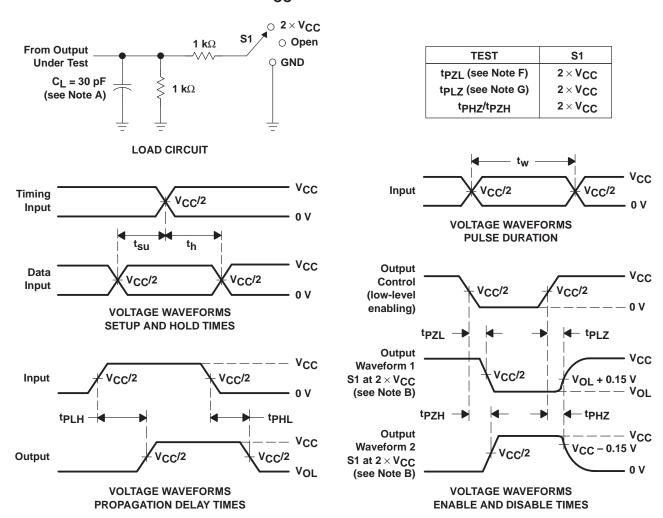
PARAMETER FROM (INPUT	FROM	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
	(1141 01)		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	А	Υ	2.2	5.6	1.1	4	1.2	4	1	3	ns

operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
		TEST CONDITIONS	TYP	TYP	TYP	TYP	ONIT
C _{pd}	Power dissipation capacitance	f = 10 MHz	3	3	4	6	pF



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$

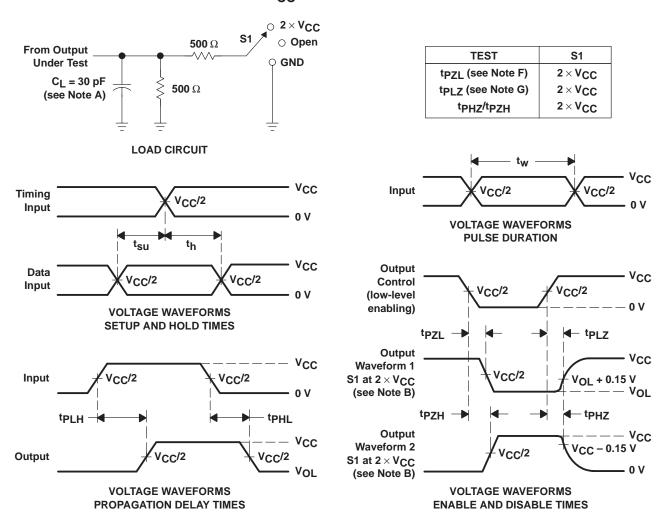


- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. Since this device has open-drain outputs, tpLz and tpzL are the same as tpd.
- F. tpzL is measured at V_{CC}/2.
- G. tpLz is measured at VoL + 0.15 V.

Figure 1. Load Circuit and Voltage Waveforms



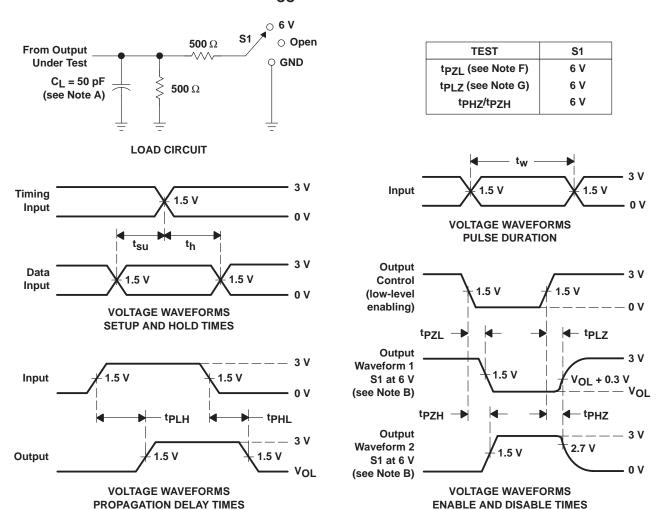
PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. Since this device has open-drain outputs, tpLz and tpzL are the same as tpd.
- F. tpzL is measured at VCC/2.
- G. tpl τ is measured at V_{OI} + 0.15 V.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$

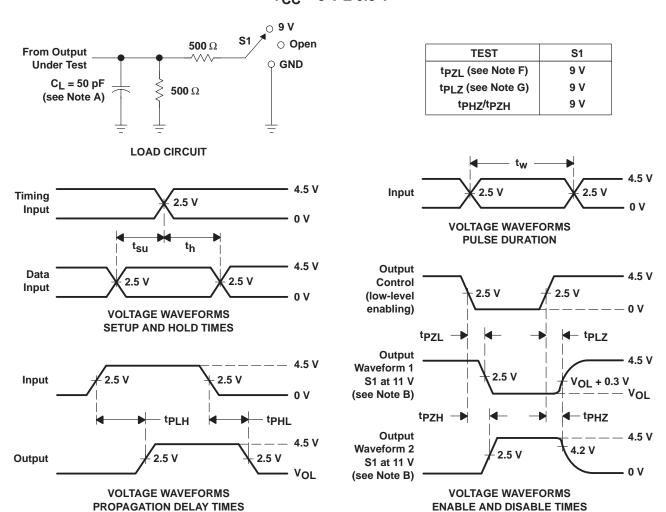


- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2.5 \text{ ns.}$
- D. The outputs are measured one at a time with one transition per measurement.
- E. Since this device has open-drain outputs, tpLz and tpzL are the same as tpd.
- F. tpz is measured at 1.5 V.
- G. t_{PLZ} is measured at V_{OL} + 0.3 V.

Figure 3. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 5 V \pm 0.5 V



- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \Omega$, $t_r \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. Since this device has open-drain outputs, tpLz and tpzL are the same as tpd.
- F. tpzL is measured at VCC/2.
- G. t_{PLZ} is measured at V_{OL} + 0.3 V.

Figure 4. Load Circuit and Voltage Waveforms

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